

IN THE SPECIFICATION:

1. Please amend the paragraph which appears at page 4, lines 10-13, of the specification, as follows:

[2] The organic luminescence device according to [1], wherein the inorganic thin film layer comprises one or more metals or compounds selected from metals, metal ~~sulfogenides~~ chalcogenides, oxynitrides, carbides, nitrides, silicides and borides.

2. Please amend the paragraph which appears at page 5, lines 10-13, of the specification, as follows:

[9] The organic luminescence device according to [8], wherein the metals in the B group are atoms belonging to any one of the groups ~~HIB, IVB, VB, VIB and VIIIB~~ 3B, 4B, 5B, 6B, and 7B in the periodic table (long period type).

3. Please amend the paragraph which appears at page 6, lines 2-4, of the specification, as follows:

[13] The organic luminescence device according to any one of [2], [3] and [7] to [12], wherein the compounds are ~~sulfogenides~~ chalcogenides or nitrides.

4. Please amend the paragraph which appears at page 9, line 26 to page 10, line 4 of the specification, as follows:

The inorganic thin film layer can be made of one or more selected from metals, and metal ~~sulfogenides~~ chalcogenides, oxynitrides, carbides, nitrides, silicides and borides. The metal(s)

may be a metal or metals in the following A group, or two or more metals wherein the A group is combined with the following B group or C group:

5. Please amend the paragraph which appears at page 10, lines 13-15 of the specification, as follows:

The inorganic thin film layer is preferably made of a ealcogenide chalcogenide and a nitride of In, Sn, Ga, Si, Ge, Zn, Cd, Mg, Al, Ta or Ti since the layer is superior in transparency.

6. Please amend the paragraph which appears at page 10, lines 20-24 of the specification, as follows:

These inorganic compounds have a small absorption coefficient, a superior transparency, and a low light-quenching capability among the A group. Thus, the compounds can make large the amount of light that can be taken out. Of the ealcogenides chalcogenides of Si, Ge, Sn, Zn, Ga, In, Cd and Mg, oxides thereof are preferable.

7. Please amend the paragraph which appears at page 13, lines 14-22 of the specification, as follows:

The inorganic thin film layer of the present invention can be made of one or more metals or compounds selected from one or more metals selected from the C group and ealcogenides chalcogenides, oxynitrides, carbides, nitrides, silicides and borides of the metals. The inorganic thin film layer can be preferably made mainly of at least one oxide selected from oxides of Ce, Pr, Nd, Sm, Eu, Gd, Tb, Dy, Ho, Er, Tm, Yb, and Lu. Specific examples and preferable examples of these oxides (the C group oxides) are as described above.

8. Please amend the paragraph which appears at page 11, line 26 to page 12, line 5, of the specification, as follows:

The metal or compound, which has a work function of 4.5 eV or more, is preferably an atom belonging to any one of the groups ~~IIIB, IVB, VB, VIIB and VIIIB~~ 3B, 4B, 5B, 6B, and 7B in the periodic table (long period type); or a compound thereof. Preferable are Au, Ni, Bi, Cr, Ir, Nb, Pt, W, Mo, Ta, Pd, Ru, Ce, V, Zr, Re and Co, and oxides, carbides, nitrides, silicides and borides thereof. These may be used alone or in combination.